



AO3701

P-Channel Enhancement Mode Field Effect Transistor with Schottky Diode

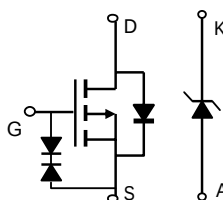
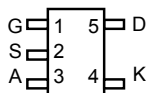
General Description

The AO3701 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications. It is ESD protected. *Standard Product AO3701 is Pb-free (meets ROHS & Sony 259 specifications). AO3701L is a Green Product ordering option. AO3701 and AO3701L are electrically identical.*

Features

$V_{DS} (V) = -20V$
 $I_D = -3A (V_{GS} = -10V)$
 $R_{DS(ON)} < 80m\Omega (V_{GS} = -10V)$
 $R_{DS(ON)} < 100m\Omega (V_{GS} = -4.5V)$
 $R_{DS(ON)} < 145m\Omega (V_{GS} = -2.5V)$
 ESD Rating: 2000V HBM
SCHOTTKY
 $V_{DS} (V) = 20V, I_F = 1A, V_F < 0.5V @ 0.5A$

SOT-23-5
Top View



Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	-20		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ^A	I_D	-3		A
		-2.3		
Pulsed Drain Current ^B	I_{DM}	-10		
Schottky reverse voltage	V_{KA}		20	V
Continuous Forward Current ^A	I_F		2	A
			1	
Pulsed Forward Current ^B	I_{FM}		10	
Power Dissipation	P_D	1.14	0.92	W
		0.72	0.59	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	80.3	110	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		117	150	
Maximum Junction-to-Lead ^C	Steady-State	R _{θJL}	43	80	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	109.4	135	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		136.5	175	
Maximum Junction-to-Lead ^C	Steady-State	R _{θJL}	58.5	80	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V, V _{GS} =0V T _J =55°C			-0.5 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±10V			±1	μA
		V _{DS} =0V, V _{GS} =±12V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.6	-0.9	-1.4	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-10			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3A T _J =125°C		65 91	80 110	mΩ
		V _{GS} =-4.5V, I _D =-2A		82	100	mΩ
		V _{GS} =-2.5V, I _D =-1A		117	145	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-3A		6.8		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V	-0.65	-0.8	-0.95	V
I _S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz		512	620	pF
C _{oss}	Output Capacitance			77		pF
C _{rss}	Reverse Transfer Capacitance			62		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		9.2	13	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-3A		5.5	6.6	nC
Q _{gs}	Gate Source Charge			0.8		nC
Q _{gd}	Gate Drain Charge			1.9		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-10V, R _L =2.8Ω, R _{GEN} =3Ω		5		ns
t _r	Turn-On Rise Time			6.7		ns
t _{D(off)}	Turn-Off DelayTime			28		ns
t _f	Turn-Off Fall Time			13.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-3A, dI/dt=100A/μs		9.8	12	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-3A, dI/dt=100A/μs		2.7		nC
SCHOTTKY PARAMETERS						
V _F	Forward Voltage Drop	I _F =0.5A		0.39	0.45	V
I _{rm}	Maximum reverse leakage current	V _R =16V			0.1	mA
		V _R =16V, T _J =125°C			20	
C _T	Junction Capacitance	V _R =10V		34		pF
t _{rr}	Schottky Reverse Recovery Time	I _F =1A, dI/dt=100A/μs		5.2	10	ns
Q _{rr}	Schottky Reverse Recovery Charge	I _F =1A, dI/dt=100A/μs		0.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t_{θJA} ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev1: May 2006

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

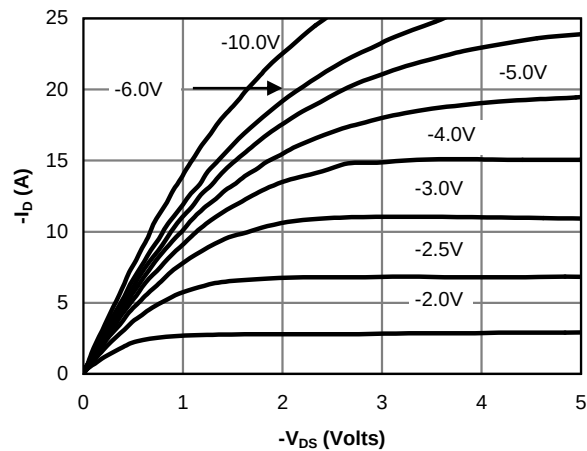


Fig 1: On-Region Characteristics

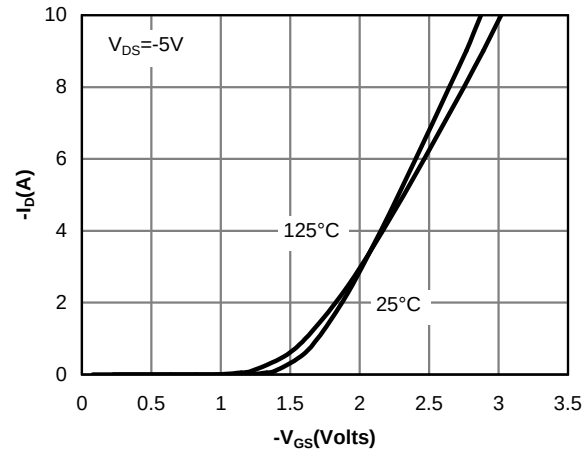


Figure 2: Transfer Characteristics

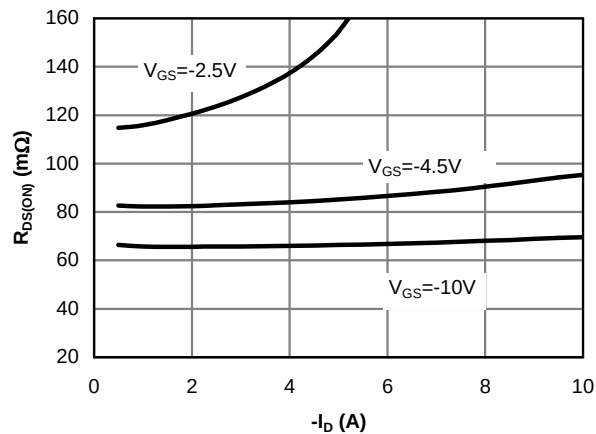


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

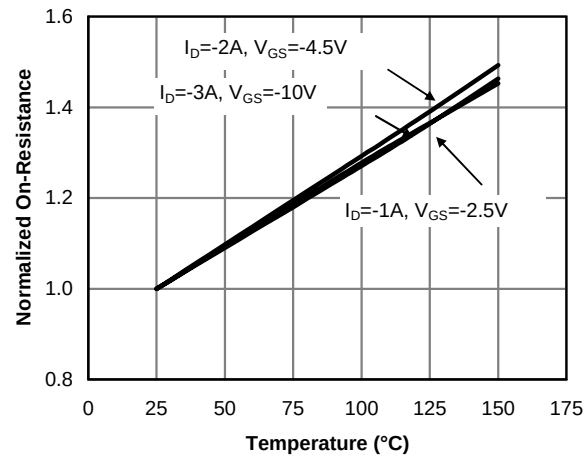


Figure 4: On-Resistance vs. Junction Temperature

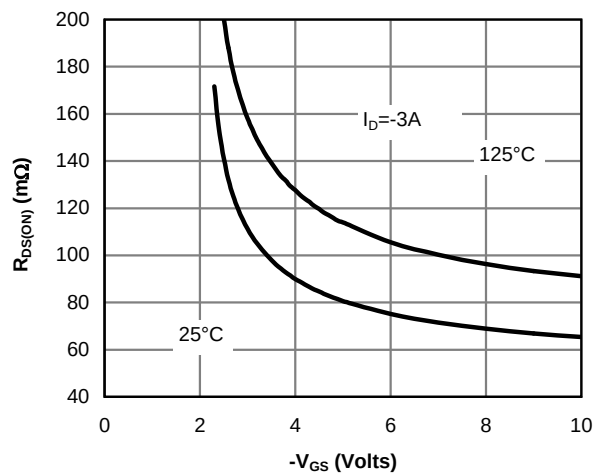


Figure 5: On-Resistance vs. Gate-Source Voltage

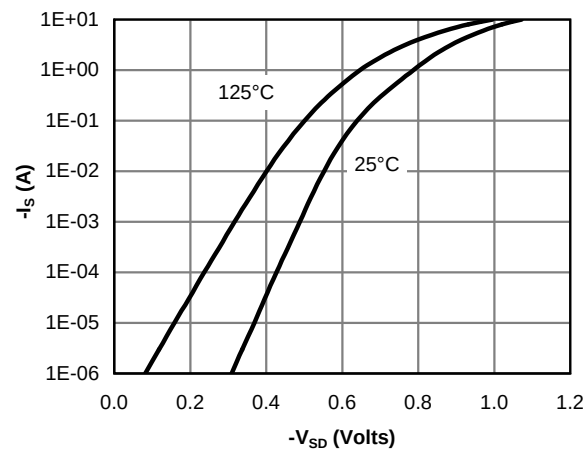
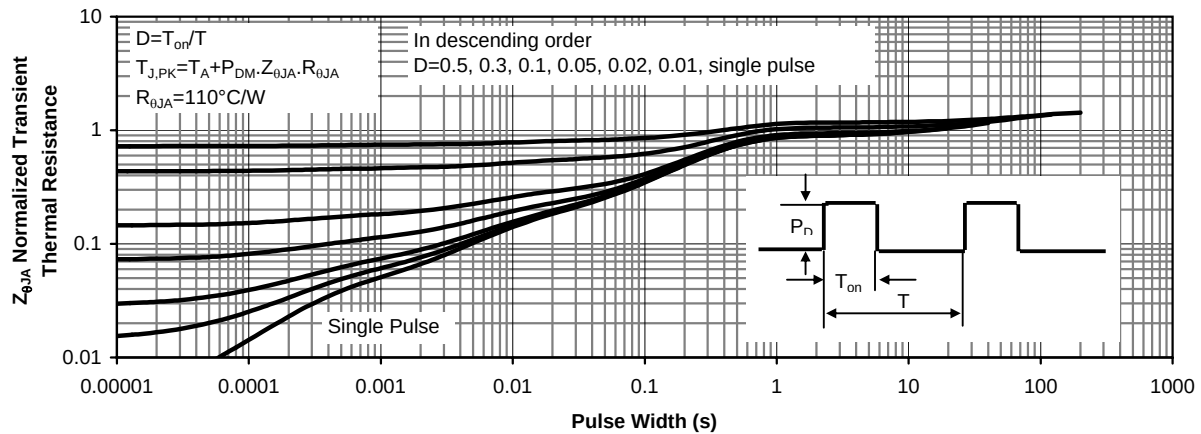
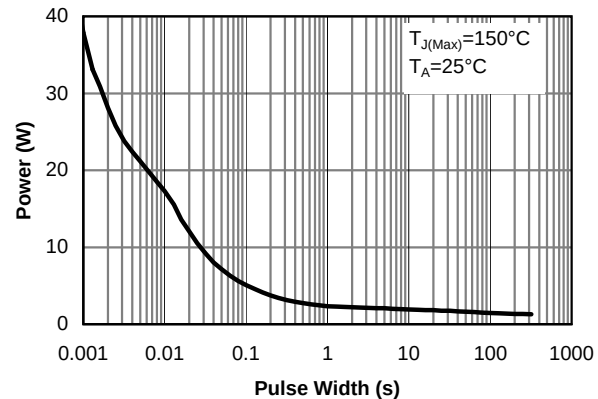
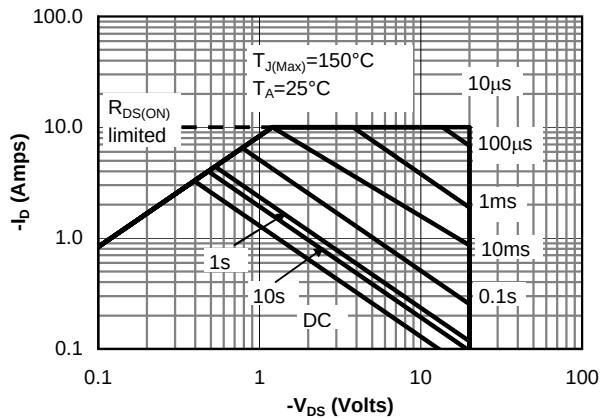
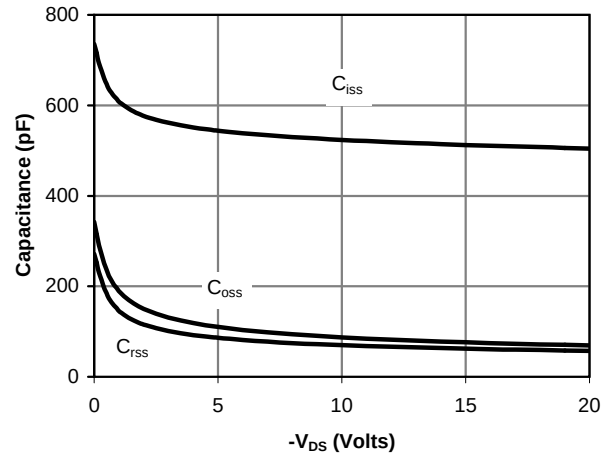
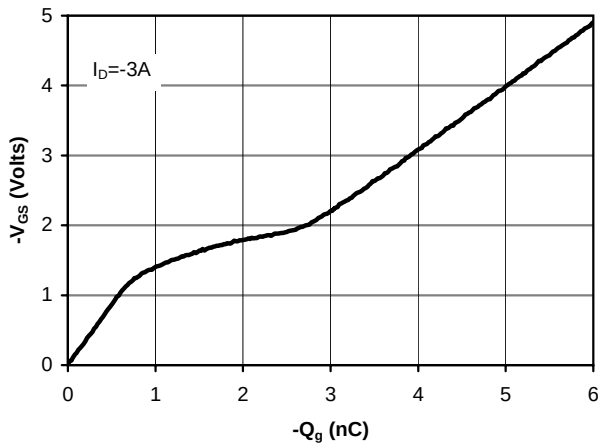


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: SCHOTTKY

